TOSHIBA Insulated Gate Bipolar Transistor Silicon N Channel IGBT

GT20J321

High Power Switching Applications Fast Switching Applications

- Fourth-generation IGBT
- Enhancement mode type
- Fast switching (FS): Operating frequency up to 50 kHz (reference)

High speed: $t_f = 0.04 \mu s$ (typ.)

Low switching loss : $E_{on} = 0.40 \text{ mJ (typ.)}$

 $E_{off} = 0.43 \text{ mJ (typ.)}$

- Low saturation voltage: VCE (sat) = 2.0 V (typ.)
- FRD included between emitter and collector

Maximum Ratings (Ta = 25°C)

Characteristics		Symbol	Rating	Unit	
Collector-emitter voltage		V _{CES}	600	V	
Gate-emitter voltage		V _{GES}	±20	V	
Collector current	DC	I _C	20	А	
	1 ms	I _{CP}	40		
Emitter-collector forward current	DC	IF	20	Α	
	1 ms	I _{FM}	40		
Collector power dissipation (Tc = 25°C)		P _C	45	W	
Junction temperature		Tj	150	°C	
Storage temperature range		T _{stg}	-55 to 150	°C	

Unit: mm 10±0.3 0.75±0.15 1. GATE 2. COLLECTOR 3. EMITTER JEDEC JEITA TOSHIBA 2-10R1C

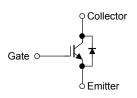
Weight: 1.7 g (typ.)

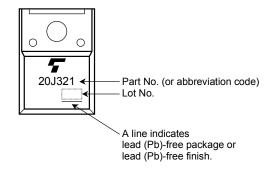
Thermal Characteristics

Characteristics	Symbol	Max	Unit
Thermal resistance (IGBT)	R _{th (j-c)}	2.78	°C/W
Thermal resistance (diode)	R _{th (j-c)}	4.23	°C/W

Equivalent Circuit

Marking

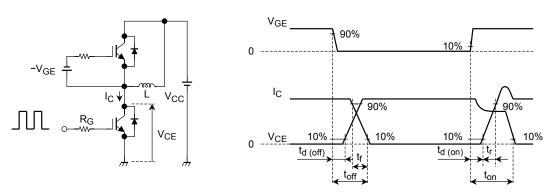




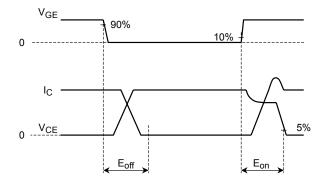
Electrical Characteristics (Ta = 25°C)

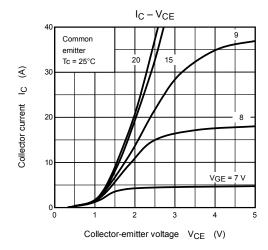
Cha	racteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Gate leakage current		I _{GES}	V _{GE} = ±20 V, V _{CE} = 0	_	_	±500	nA
Collector cut-off	current	I _{CES}	V _{CE} = 600 V, V _{GE} = 0	_	_	1.0	mA
Gate-emitter cut-off voltage		V _{GE} (OFF)	I _C = 2 mA, V _{CE} = 5 V	3.5	_	6.5	V
Collector-emitter saturation voltage		V _{CE (sat)}	I _C = 20 A, V _{GE} = 15 V	_	2.0	2.45	V
Input capacitance		C _{ies}	V _{CE} = 10 V, V _{GE} = 0, f = 1 MHz	_	3000	_	pF
Switching time	Turn-on delay time	t _{d (on)}	Inductive Load $V_{CC}=300 \text{ V, } I_{C}=20 \text{ A}$ $V_{GG}=+15 \text{ V, } R_{G}=33 \Omega \tag{Note 1}$ (Note 2)	_	0.06	_	μs
	Rise time	t _r		_	0.04	_	
	Turn-on time	t _{on}		_	0.17	_	
	Turn-off delay time	t _{d (off)}		_	0.24	_	
	Fall time	t _f		_	0.04	_	
	Turn-off time	t _{off}		_	0.34	_	
Switching loss	Turn-on switching loss	E _{on}		_	0.40	_	- mJ
	Turn-off switching loss	E _{off}		_	0.43	_	
Peak forward voltage		V _F	I _F = 20 A, V _{GE} = 0	_	_	2.1	V
Reverse recovery time		t _{rr}	I _F = 20 A, di/dt = -100 A/µs	_	100	_	ns

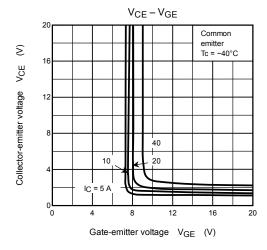
Note 1: Switching time measurement circuit and input/output waveforms

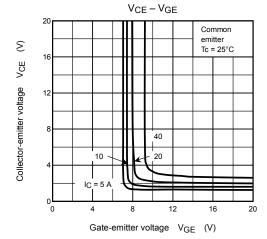


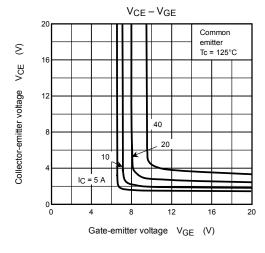
Note 2: Switching loss measurement waveforms

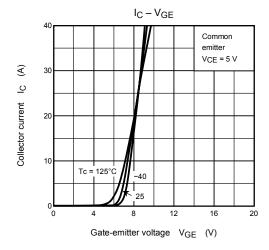


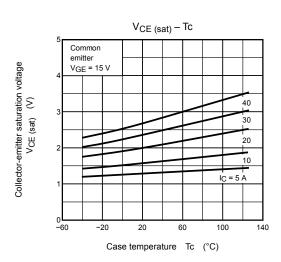


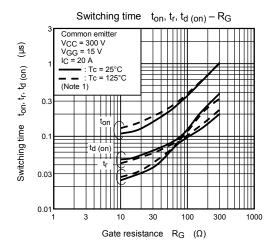


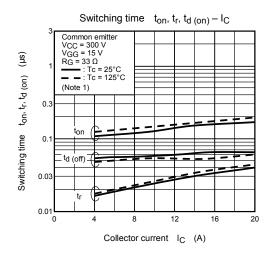


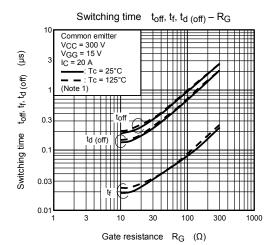


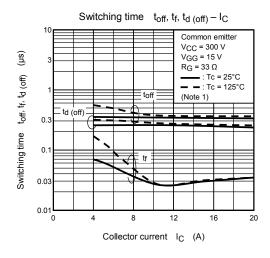


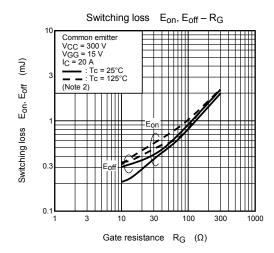


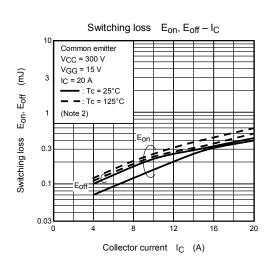




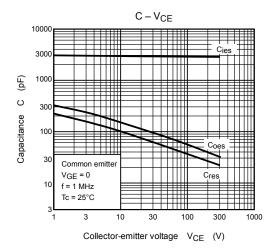


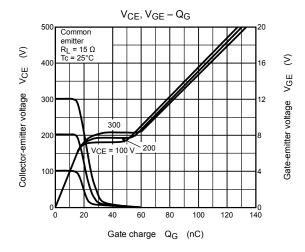


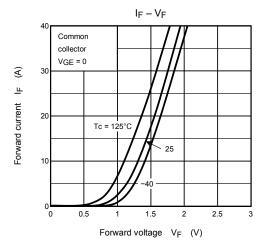


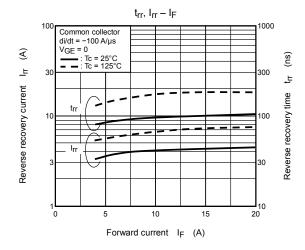


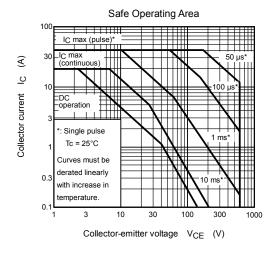
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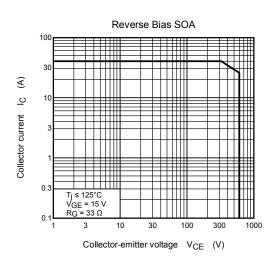




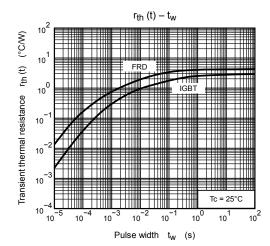








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